

Results with thin and standard p-type detectors after heavy neutron irradiation

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OUTLINE:

- Introduction
- Motivations for using p-type substrates in high radiation environments
- Motivations for investigating thin (140µm) vs standard (300µm) detectors
- Charge Collection Efficiency results up to 1x10¹⁶ n cm⁻²
- Summary and future work

N-side read-out for tracking in high radiation environments?

Schematic changes of Electric field after irradiation



Effect of trapping on the Charge Collection Efficiency (CCE)

$$Q_{tc} \cong Q_0 exp(-t_c/\tau_{tr}), 1/\tau_{tr} = \beta \Phi.$$

Collecting electrons provide a sensitive advantage with respect to holes due to a much shorter t_c . P-type detectors are the most natural solution for *e* collection on the segmented side.

N-side read out to keep lower t_c

Effect of trapping on the Charge Collection Distance

$$Q_{tc} \cong Q_0 \exp(-t_c/\tau_{tr}), \ 1/\tau_{tr} = \beta \Phi.$$
$$v_{sat,e} \ge \tau_{tr} = \lambda_{av}$$

 $\beta_e = 4.2E - 16 \text{ cm}^{-2}/\text{ns}$

 $\beta_{\rm h} = 6.1 \text{E} - 16 \text{ cm}^{-2}/\text{ns}$

From G. Kramberger et al., NIMA 476(2002), 645-651.

After heavy irradiation thin detectors should have a similar CCE as thicker ones.

 $\lambda_{av} (\Phi = 1e14) \cong 2400 \mu m$

 $\lambda_{av} (\Phi = 1e16) \cong 24 \mu m$

Silicon miniature microstrip detectors and irradiation

RD50 mask (see: http://rd50.web.cern.ch/rd50/)

Mini microstrip, ~1x1 cm², 128 strips, 80 µm pitch, designed by Liverpool and produced by Micron on 300µm and 140µm thick wafers.

Irradiation and dosimetry: TRIGA Mark II research reactor Reactor Centre of the Jozef Stefan Institute, Ljubljana, Slovenia



Method: measure the charge collection of the segmented devices using an analogue electronics chip (SCT128) clocked at LHC speed (40MHz clk, 25ns shaping time). The system is calibrated to the most probable value of the m.i.p. energy loss in a non-irradiated $300\mu m$ thick detector (~23000 e⁻).

Fast electron source: ⁹⁰Sr, triggered with scintillators in coincidence.



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Results with neutron irradiated Micron detectors



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A correction of the result at 5x10¹⁴ n cm⁻²

Comparison of the measurements on $30k\Omega$ Micron detectors irradiated to the nominal Φ of $5x10^{14}$ cm⁻² in March 2006 and October 2007



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Results with neutron irradiated Micron detectors



Charge collection efficiency vs fluence for micro-strip detectors irradiated with n and p read-out at LHC speed (40MHz, SCT128 chip).



Comparison of CCE with 140 μ m and 300 μ m thick detectors from Micron irradiated to various n fluences, up to 1x10¹⁶ cm⁻²!



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Comparison of CCE with 140 μ m and 300 μ m thick detectors from Micron irradiated to various n fluences, up to 1x10¹⁶ cm⁻²!



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Ratio of the charge collected by thick to thin detectors as a function of fluence



Annealing of irradiated dettectors after 1x10¹⁶ n cm⁻²



Ratio of the charge collected by thick to thin detectors as a function of the annealing time for detectors irradiated to 1x10¹⁶ n cm⁻²



CONCLUSIONS:

P-type detectors tested up to 1x10¹⁶ n cm⁻² show a extremely good signal and adequate radiation tolerance for the LHC upgrade to 10 times higher luminosity.

These measurements are the first reference measurements for highly segmented silicon detector made in planar technology (microstrip and pixel detectors) at these doses!

After heavy irradiations the CCE of thin and thick detectors becomes similar. The choice of optimal thickness can be dictated by the need of reducing the detector mass rather than increase of the signal after irradiation (at least up the remarkable dose of $1x10^{16}$ n cm⁻²!!).

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